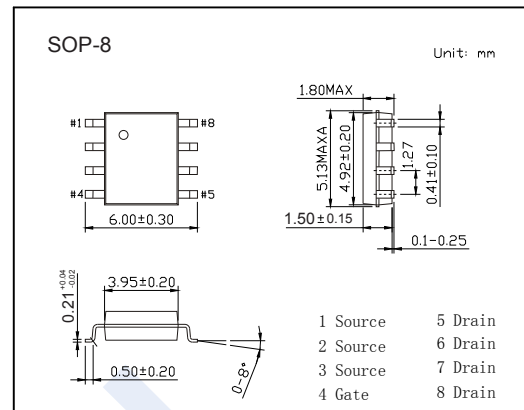
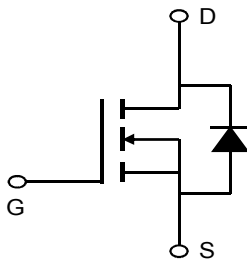


N-Channel MOSFET

AO4266 (KO4266)

■ Features

- $V_{DS} = 60V$
- $I_D = 10 A$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 15m\Omega$ ($V_{GS} = 10V$)
- $R_{DS(ON)} < 19m\Omega$ ($V_{GS} = 4.5V$)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

| Parameter | Symbol | Rating | Unit | |
|---|-------------|------------------|------------|--------------|
| Drain-Source Voltage | V_{DS} | 60 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| VDS Spike @ 10us | V_{SPIKE} | 72 | | |
| Continuous Drain Current | I_D | $T_A=25^\circ C$ | 10 | A |
| | | $T_A=70^\circ C$ | 8 | |
| Pulsed Drain Current | I_{DM} | 40 | | |
| Avalanche Current | I_{AS} | 20 | | |
| Avalanche Energy | $L=0.1mH$ | E_{AS} | 20 | mJ |
| Power Dissipation | P_D | $T_A=25^\circ C$ | 3.1 | W |
| | | $T_A=70^\circ C$ | 2 | |
| Thermal Resistance.Junction- to-Ambient | R_{thJA} | $t \leq 10s$ | 40 | $^\circ C/W$ |
| | | Steady-State | 75 | |
| Thermal Resistance.Junction- to-Lead | R_{thJL} | 24 | | |
| Junction Temperature | T_J | 150 | $^\circ C$ | |
| Storage Temperature Range | T_{stg} | -55 to 150 | | |

N-Channel MOSFET

AO4266 (KO4266)

■ Electrical Characteristics Ta = 25°C

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit | |
|---------------------------------------|---------------------|---|--|------|------|------|-----|
| Drain-Source Breakdown Voltage | V _{DSS} | I _D =250 uA, V _{GS} =0V | 60 | | | V | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{Ds} =60V, V _{GS} =0V | | | 1 | uA | |
| | | V _{Ds} =60V, V _{GS} =0V, T _J =55°C | | | 5 | | |
| Gate-Body Leakage Current | I _{GSS} | V _{Ds} =0V, V _{GS} =±20V | | | ±100 | nA | |
| Gate Threshold Voltage | V _{GS(th)} | V _{Ds} =V _{GS} , I _D =250uA | 1.5 | | 2.5 | V | |
| Static Drain-Source On-Resistance | R _{DS(on)} | V _{GS} =10V, I _D =10A | | | 15 | m Ω | |
| | | V _{GS} =10V, I _D =10A T _J =125°C | | | 25 | | |
| | | V _{GS} =4.5V, I _D =9A | | | 19 | | |
| Forward Transconductance | g _{FS} | V _{Ds} =5V, I _D =10A | | 35 | | S | |
| Input Capacitance | C _{iss} | V _{GS} =0V, V _{Ds} =30V, f=1MHz | | 1340 | | pF | |
| Output Capacitance | C _{oss} | | | 123 | | | |
| Reverse Transfer Capacitance | C _{rss} | | | 10 | | | |
| Gate Resistance | R _g | | V _{GS} =0V, V _{Ds} =0V, f=1MHz | 0.7 | | | 2.3 |
| Total Gate Charge (10V) | Q _g | V _{GS} =10V, V _{Ds} =30V, I _D =10A | | 21 | 30 | nC | |
| Total Gate Charge (4.5V) | | | | 9 | 15 | | |
| Gate Source Charge | | | Q _{gs} | | 4.7 | | |
| Gate Drain Charge | | | Q _{gd} | | 2.6 | | |
| Turn-On DelayTime | t _{d(on)} | V _{GS} =10V, V _{Ds} =30V, R _L =3Ω, R _{GEN} =3Ω | | 6 | | ns | |
| Turn-On Rise Time | t _r | | | 2.5 | | | |
| Turn-Off DelayTime | t _{d(off)} | | | 22 | | | |
| Turn-Off Fall Time | t _f | | | 2.5 | | | |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 10A, di/dt= 500A/us | | 15.5 | | nC | |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 55.5 | | | |
| Maximum Body-Diode Continuous Current | I _S | | | | 4 | A | |
| Diode Forward Voltage | V _{SD} | I _S =1A, V _{GS} =0V | | | 1 | V | |

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

| | |
|---------|----------------|
| Marking | 4266 KC**** |
|---------|----------------|

N-Channel MOSFET AO4266 (KO4266)

■ Typical Characteristics

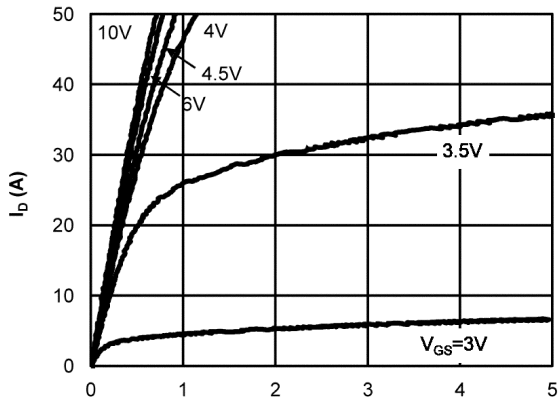


Figure 1: On-Region Characteristics (Note E)

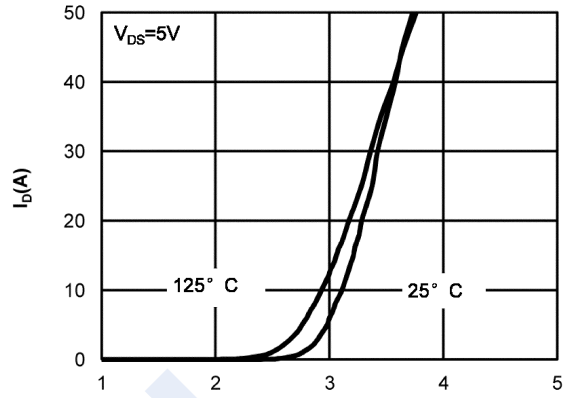


Figure 2: Transfer Characteristics (Note E)

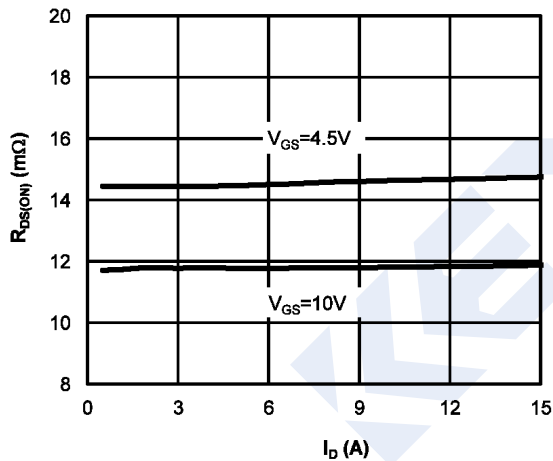


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

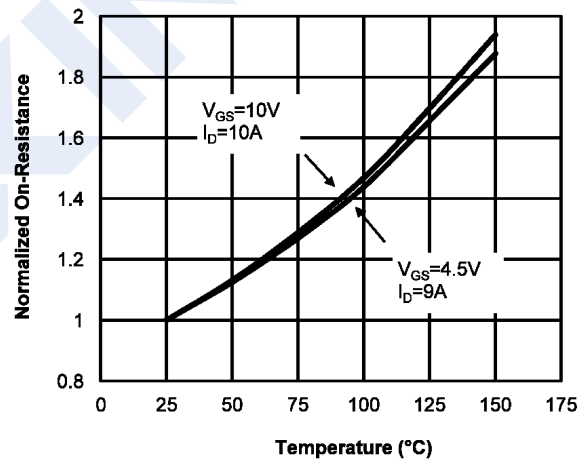


Figure 4: On-Resistance vs. Junction Temperature (Note E)

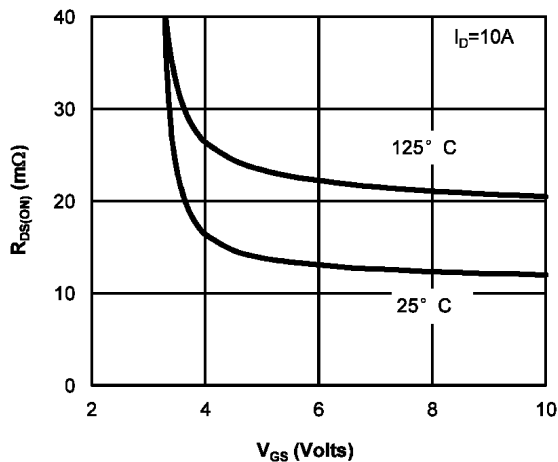


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

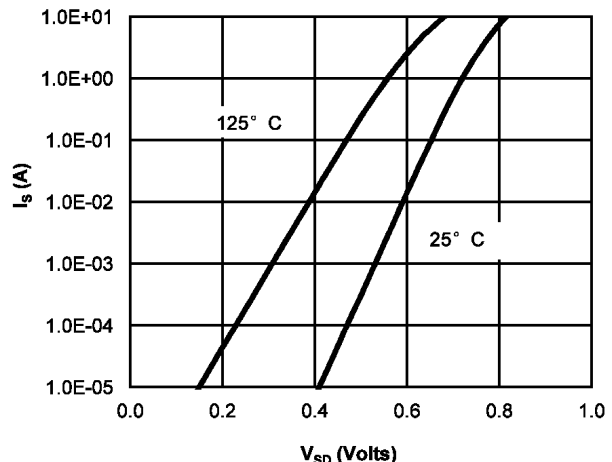


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET AO4266 (KO4266)

■ Typical Characteristics

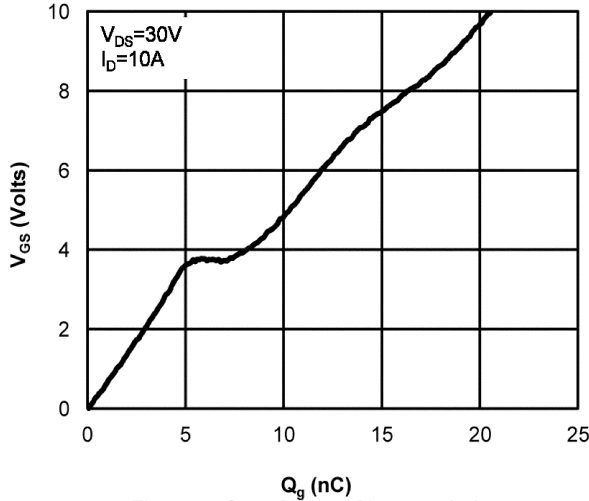


Figure 7: Gate-Charge Characteristics

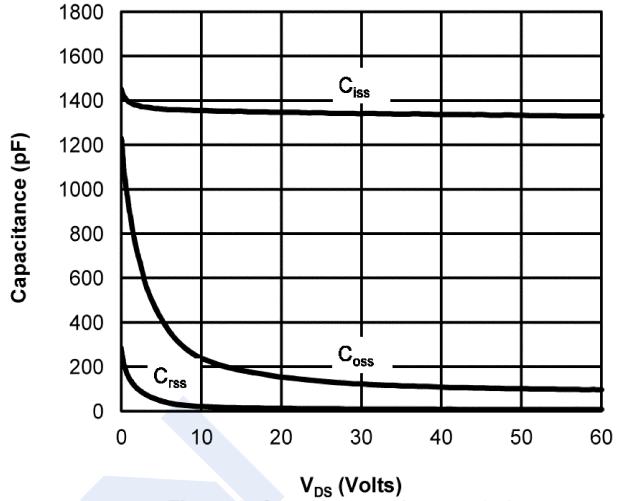


Figure 8: Capacitance Characteristics

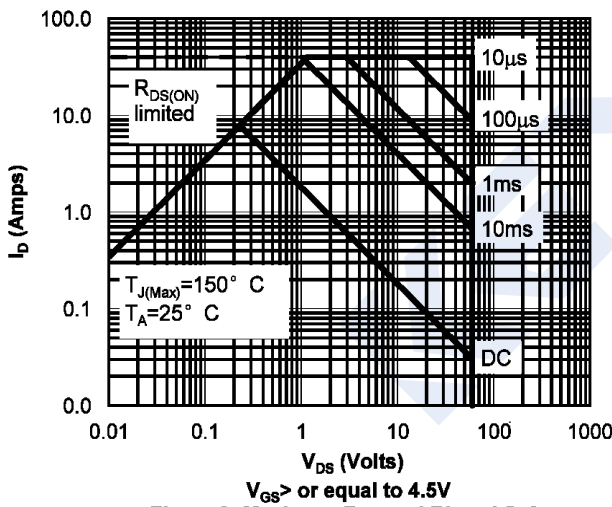


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

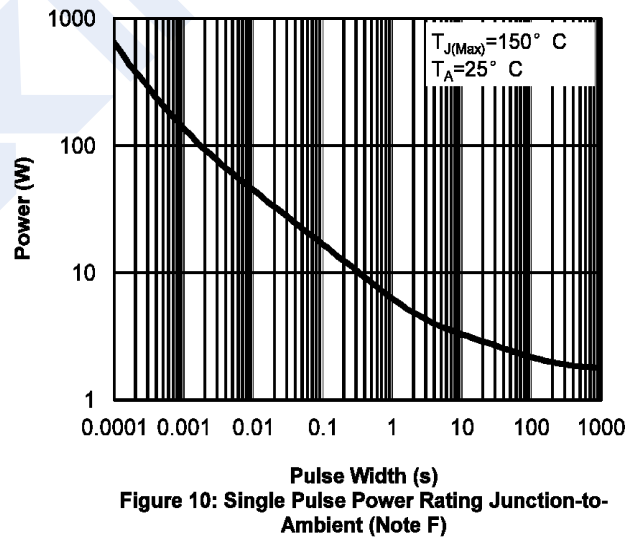


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

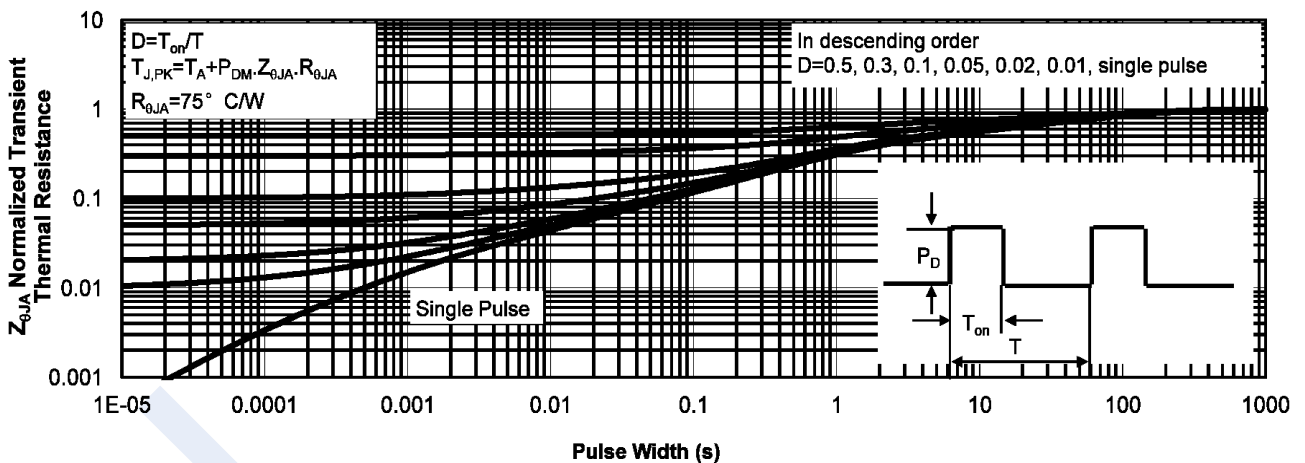


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)